

Dual N-Channel MOSFET

30V, 20A, 20mΩ

FEATURES

- Fast switching
- 100% avalanche tested
- Pb-free plating
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

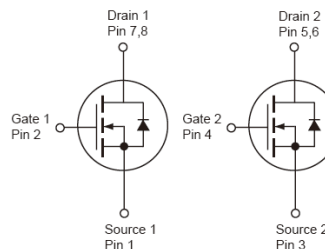
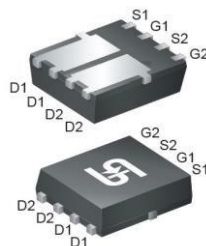
APPLICATIONS

- Power Supply
- Motor Control

KEY PERFORMANCE PARAMETERS			
PARAMETER		VALUE	UNIT
V_{DS}		30	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	20	mΩ
	$V_{GS} = 4.5V$	30	
Q_g		4.1	nC



PDFN33 Dual



Dual N-Channel MOSFET

Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 1)	I_D	$T_C = 25^\circ\text{C}$	20
		$T_C = 100^\circ\text{C}$	13
Pulsed Drain Current (Note 2)	I_{DM}	80	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_{DTOT}	20	W
Single Pulsed Avalanche Energy (Note 3)	E_{AS}	14	mJ
Single Pulsed Avalanche Current (Note 3)	I_{AS}	17	A
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to 150	$^\circ\text{C}$

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	6.4	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	62	$^\circ\text{C/W}$

Notes: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 PCB in still air

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	BV_{DSS}	30	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(TH)}$	1.2	1.5	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$	I_{DSS}	--	--	1	μA
	$V_{DS} = 24\text{V}, T_C = 125^\circ\text{C}$		--	--	10	
Drain-Source On-State Resistance	$V_{GS} = 10\text{V}, I_D = 10\text{A}$	$R_{DS(on)}$	--	17	20	m Ω
	$V_{GS} = 4.5\text{V}, I_D = 6\text{A}$		--	23	30	
Forward Transconductance	$V_{DS} = 5\text{V}, I_D = 6\text{A}$	g_{fs}	--	13	--	S
Dynamic (Note 5)						
Total Gate Charge	$V_{DS} = 15\text{V}, I_D = 8\text{A}, V_{GS} = 4.5\text{V}$	Q_g	--	4.1	--	nC
Gate-Source Charge		Q_{gs}	--	1	--	
Gate-Drain Charge		Q_{gd}	--	2.1	--	
Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	C_{ISS}	--	345	--	pF
Output Capacitance		C_{OSS}	--	55	--	
Reverse Transfer Capacitance		C_{RSS}	--	32	--	
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 15\text{V}, I_D = 1\text{A}, R_{GEN} = 6\Omega$	$t_{d(on)}$	--	2.8	--	ns
Turn-On Rise Time		t_r	--	7.2	--	
Turn-Off Delay Time		$t_{d(off)}$	--	15.8	--	
Turn-Off Fall Time		t_f	--	4.6	--	
Source-Drain Diode (Note 4)						
Maximum Continuous Drain-Source Diode Forward Current	Integral reverse diode in the MOSFET	I_S	--	--	20	A
Maximum Pulse Drain-Source Diode Forward Current		I_{SM}	--	--	80	A
Diode-Source Forward Voltage	$V_{GS} = 0\text{V}, I_S = 1\text{A}$	V_{SD}	--	--	1	V

Notes:

- Current limited by package
- Pulse width limited by the maximum junction temperature
- $L = 0.1\text{mH}, I_{AS} = 17\text{A}, V_{DD} = 25\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
- Pulse test: $PW \leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- For DESIGN AID ONLY, not subject to production testing.
- Switching time is essentially independent of operating temperature.

ORDERING INFORMATION

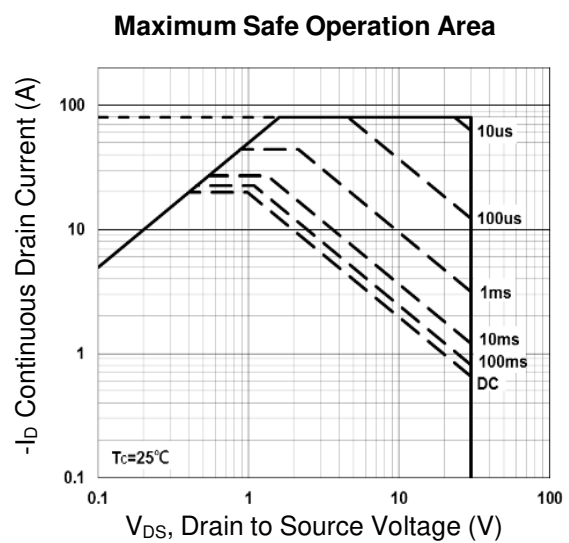
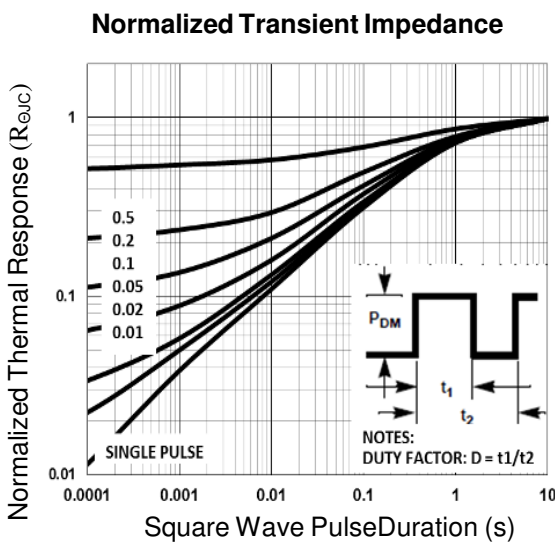
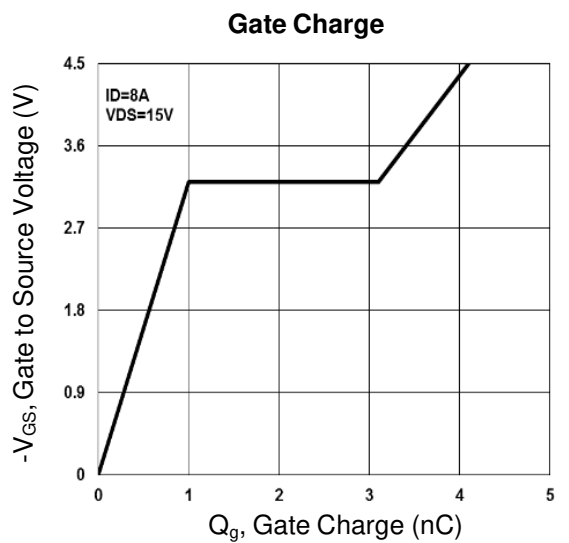
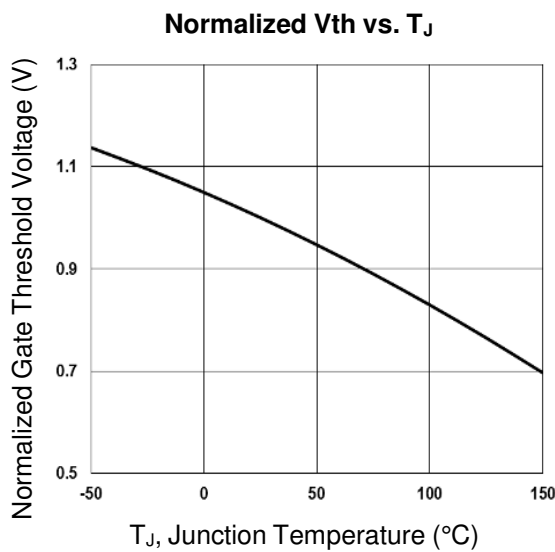
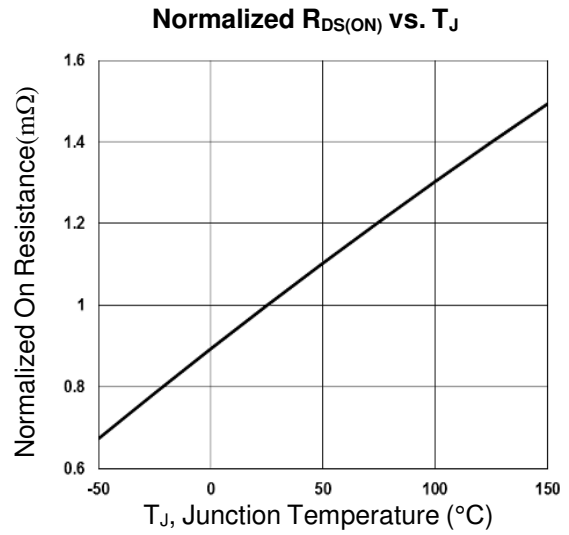
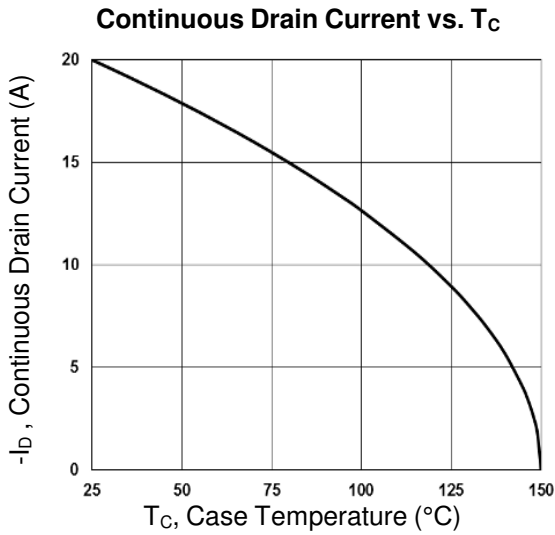
PART NO.	PACKAGE	PACKING
TSM200N03DPQ33 RGG	PDFN33 Dual	5Kpcs / 13"Reel

Note:

1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
2. Halogen-free according to IEC 61249-2-21 definition

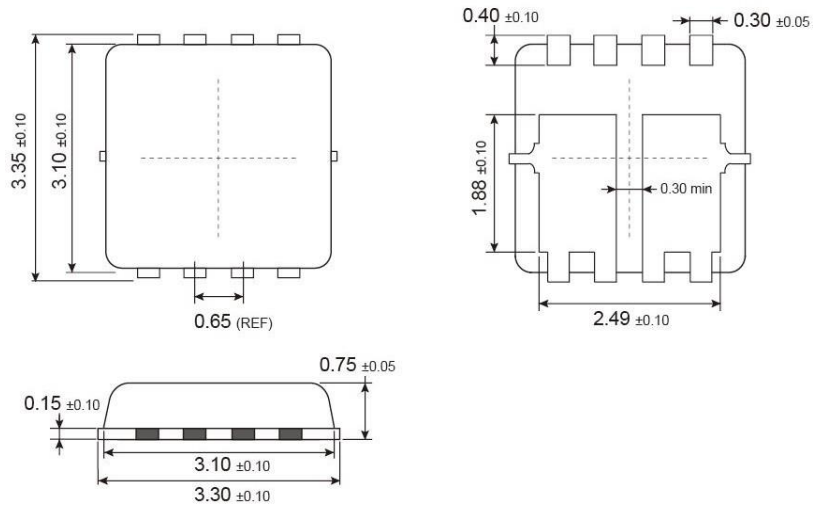
CHARACTERISTICS CURVES

($T_C = 25^\circ\text{C}$ unless otherwise noted)

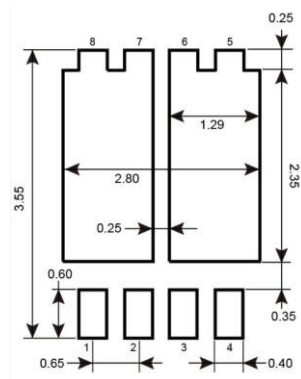


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

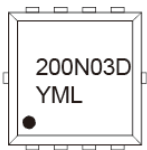
PDFN33 Dual



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



- Y = Year Code
- M = Month Code for Halogen Free Product
 - O =Jan P =Feb Q =Mar R =Apr
 - S =May T =Jun U =Jul V =Aug
 - W =Sep X =Oct Y =Nov Z =Dec
- L = Lot Code (1~9, A~Z)

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